

74HC365-Q100; 74HCT365-Q100

Hex buffer/line driver; 3-state

Rev. 1 — 2 August 2012

Product data sheet

1. General description

The 74HC365-Q100; 74HCT365-Q100 is a hex buffer/line driver with 3-state outputs controlled by the output enable inputs ($\overline{OEn}$). A HIGH on $\overline{OEn}$ causes the outputs to assume a high impedance OFF-state. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

The 74HC365-Q100; 74HCT365-Q100 is functionally identical to:

- 74HC366-Q100; 74HCT366-Q100, but has non-inverting outputs

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Inverting outputs
- Input levels:
 - ◆ For 74HC365-Q100: CMOS level
 - ◆ For 74HCT365-Q100: TTL level
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Multiple package options

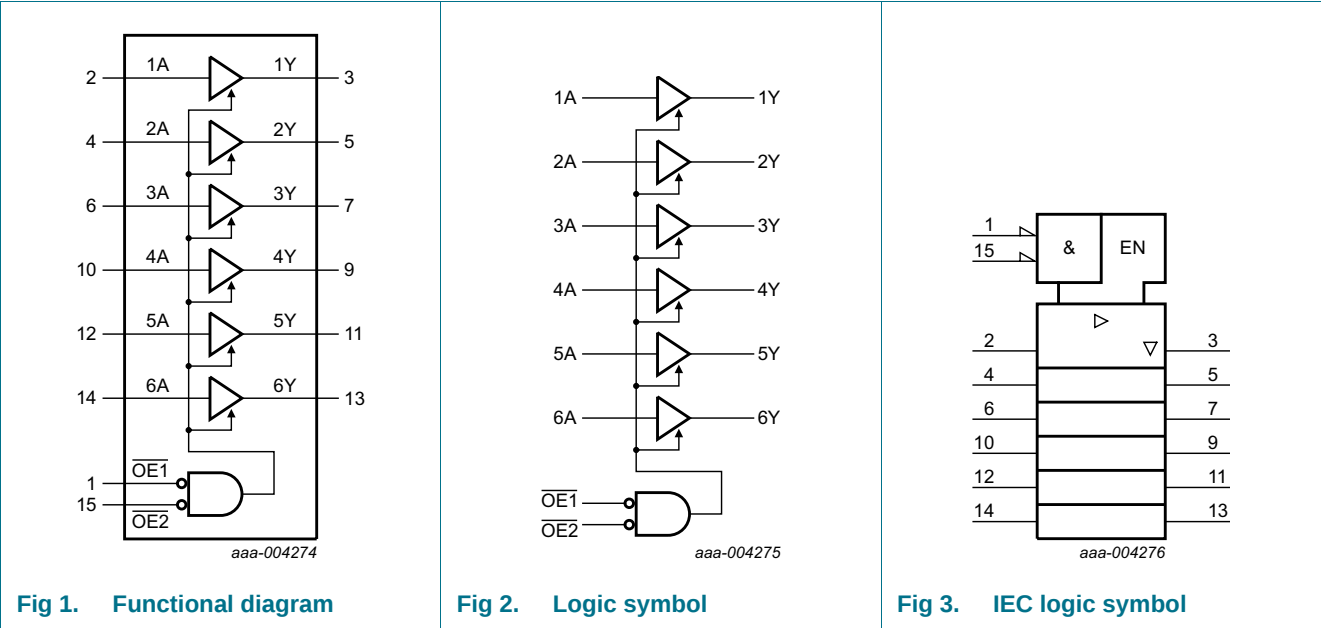


3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC365-Q100				
74HC365D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC365PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT365-Q100				
74HCT365D-Q100	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT365PW-Q100	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram



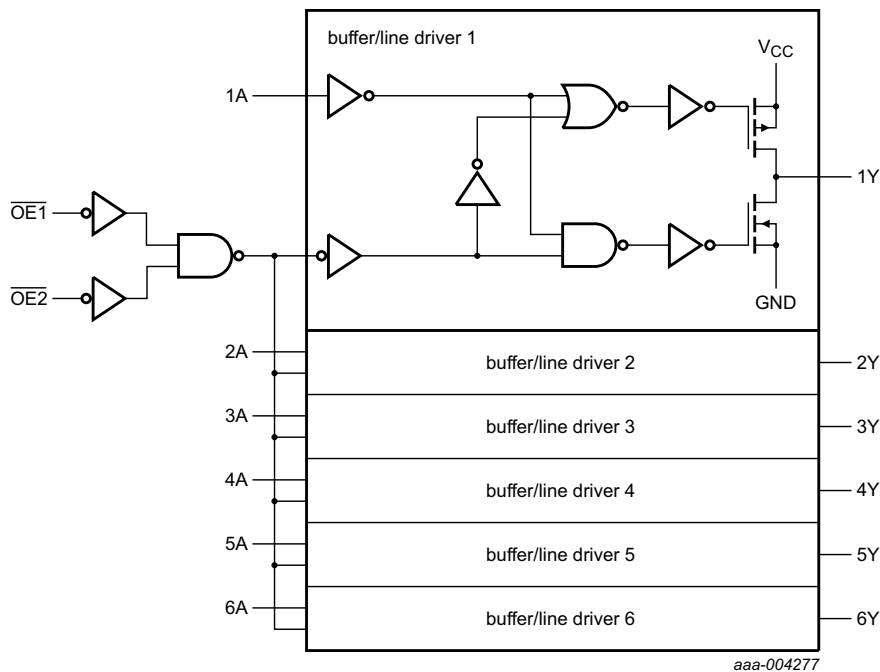


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning

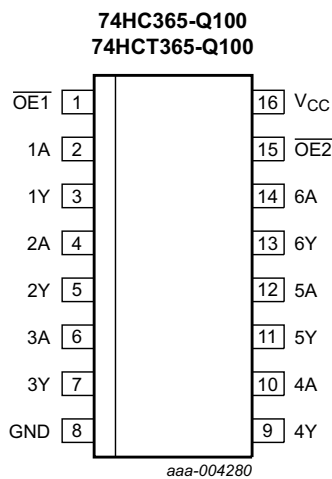


Fig 5. Pin configuration

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{\text{OE1}}$	1	output enable input 1 (active LOW)
1A	2	data input 1
1Y	3	data output 1
2A	4	data input 2
2Y	5	data output 2
3A	6	data input 3
3Y	7	data output 3
GND	8	ground (0 V)
4Y	9	data output 4
4A	10	data input 4
5Y	11	data output 5
5A	12	data input 5
6Y	13	data output 6
6A	14	data input 6
$\overline{\text{OE2}}$	15	output enable input 2 (active LOW)
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Control		Input	Output
$\overline{\text{OE1}}$	$\overline{\text{OE2}}$	nA	nY
L	L	L	L
L	L	H	H
X	H	X	Z
H	X	X	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	-	± 35	mA
I_{CC}	supply current		-	70	mA
I_{GND}	ground current		-	-70	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	SO16 package	[1] -	500	mW
		TSSOP16 package	[2] -	500	mW

[1] For SO16 packages: P_{tot} derates linearly with 8 mW/K above 70 °C.

[2] For TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC365-Q100			74HCT365-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics 74HC365-Q100

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	-	-	-	
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	2.0	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	4.5	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	6.0	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.5	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	µA
C _I	input capacitance		-	3.5	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.84	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.34	-	-	V

Table 6. Static characteristics 74HC365-Q100 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.33	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V;	-	-	±1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±5.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	80	µA
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	V
		V _{CC} = 4.5 V	3.15	-	-	V
		V _{CC} = 6.0 V	4.2	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	V
		V _{CC} = 4.5 V	-	-	1.35	V
		V _{CC} = 6.0 V	-	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 2.0 V	1.9	-	-	V
		I _O = -20 µA; V _{CC} = 4.5 V	4.4	-	-	V
		I _O = -20 µA; V _{CC} = 6.0 V	5.9	-	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.7	-	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.2	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±10.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	160	µA

Table 7. Static characteristics 74HCT365-Q100

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 µA	4.4	4.5	-	V
		I _O = -6.0 mA	3.98	4.32	-	V

Table 7. Static characteristics 74HCT365-Q100 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	0	0.1	V
		I _O = 6.0 mA	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	±0.5	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; I _O = 0 A				
		pins nA	-	100	360	μA
		pin $\overline{\text{OE1}}$	-	100	360	μA
		pin $\overline{\text{OE2}}$	-	90	324	μA
C _I	input capacitance		-	3.5	-	pF
T _{amb} = –40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = –20 μA	4.4	-	-	V
		I _O = –6.0 mA	3.84	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V			±5.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	80	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; I _O = 0 A				
		pins nA	-	-	450	μA
		pin $\overline{\text{OE1}}$	-	-	450	μA
		pin $\overline{\text{OE2}}$	-	-	405	μA
T _{amb} = –40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = –20 μA	4.4	-	-	V
		I _O = –6.0 mA	3.7	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	±10.0	μA

Table 7. Static characteristics 74HCT365-Q100 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	160	μ A
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $I_O = 0$ A				
		pins nA	-	-	490	μ A
		pin $\overline{OE}1$	-	-	490	μ A
		pin $\overline{OE}2$	-	-	441	μ A

10. Dynamic characteristics

Table 8. Dynamic characteristics 74HC365-Q100Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = 25$ °C						
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		$V_{CC} = 2.0$ V	-	30	95	ns
		$V_{CC} = 4.5$ V	-	11	19	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	9	-	ns
		$V_{CC} = 6.0$ V	-	9	16	ns
t_{en}	enable time	$\overline{OE}n$ to nY; see Figure 7	[2]			
		$V_{CC} = 2.0$ V	-	47	150	ns
		$V_{CC} = 4.5$ V	-	17	30	ns
		$V_{CC} = 6.0$ V	-	14	26	ns
t_{dis}	disable time	$\overline{OE}n$ to nY; see Figure 7	[3]			
		$V_{CC} = 2.0$ V	-	61	150	ns
		$V_{CC} = 4.5$ V	-	22	30	ns
		$V_{CC} = 6.0$ V	-	18	26	ns
t_t	transition time	see Figure 6	[4]			
		$V_{CC} = 2.0$ V	-	14	60	ns
		$V_{CC} = 4.5$ V	-	5	12	ns
		$V_{CC} = 6.0$ V	-	4	10	ns
C_{PD}	power dissipation capacitance	per buffer; $V_I =$ GND to V_{CC}	[5]	-	40	pF
$T_{amb} = -40$ °C to $+85$ °C						
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		$V_{CC} = 2.0$ V	-	-	120	ns
		$V_{CC} = 4.5$ V	-	-	24	ns
		$V_{CC} = 6.0$ V	-	-	20	ns
t_{en}	enable time	$\overline{OE}n$ to nY; see Figure 7	[2]			
		$V_{CC} = 2.0$ V	-	-	190	ns
		$V_{CC} = 4.5$ V	-	-	38	ns
		$V_{CC} = 6.0$ V	-	-	33	ns

Table 8. Dynamic characteristics 74HC365-Q100 ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{dis}	disable time	$\overline{OEn}$ to nY; see Figure 7 [3]				
		V _{CC} = 2.0 V	-	-	190	ns
		V _{CC} = 4.5 V	-	-	38	ns
		V _{CC} = 6.0 V	-	-	33	ns
t _t	transition time	see Figure 6 [4]				
		V _{CC} = 2.0 V	-	-	75	ns
		V _{CC} = 4.5 V	-	-	15	ns
		V _{CC} = 6.0 V	-	-	13	ns
T _{amb} = -40 °C to +125 °C						
t _{pd}	propagation delay	nA to nY; see Figure 6 [1]				
		V _{CC} = 2.0 V	-	-	145	ns
		V _{CC} = 4.5 V	-	-	29	ns
		V _{CC} = 6.0 V	-	-	25	ns
t _{en}	enable time	$\overline{OEn}$ to nY; see Figure 7 [2]				
		V _{CC} = 2.0 V	-	-	225	ns
		V _{CC} = 4.5 V	-	-	45	ns
		V _{CC} = 6.0 V	-	-	38	ns
t _{dis}	disable time	$\overline{OEn}$ to nY; see Figure 7 [3]				
		V _{CC} = 2.0 V	-	-	225	ns
		V _{CC} = 4.5 V	-	-	45	ns
		V _{CC} = 6.0 V	-	-	38	ns
t _t	transition time	see Figure 6 [4]				
		V _{CC} = 2.0 V	-	-	90	ns
		V _{CC} = 4.5 V	-	-	18	ns
		V _{CC} = 6.0 V	-	-	15	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

[2] t_{en} is the same as t_{PZH} and t_{PZL} .

[3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .

[4] t_t is the same as t_{THL} and t_{TLH} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

Table 9. Dynamic characteristics 74HCT365-Q100

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		V _{CC} = 4.5 V	-	14	25	ns
		V _{CC} = 5 V; C _L = 15 pF	-	11	-	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[2]	18	35	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[3]	23	35	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	[4]	5	12	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to (V _{CC} - 1.5 V)	[5]	40	-	pF
T_{amb} = -40 °C to +85 °C						
t _{pd}	propagation delay	nA to nY; V _{CC} = 4.5 V; see Figure 6	[1]	-	31	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[2]	-	44	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[3]	-	44	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	[4]	-	15	ns
T_{amb} = -40 °C to +125 °C						
t _{pd}	propagation delay	nA to nY; V _{CC} = 4.5 V; see Figure 6	[1]	-	38	ns
t _{en}	enable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[2]	-	53	ns
t _{dis}	disable time	OEn to nY; V _{CC} = 4.5 V; see Figure 7	[3]	-	53	ns
t _t	transition time	V _{CC} = 4.5 V; see Figure 6	[4]	-	18	ns

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_{en} is the same as t_{PZH} and t_{PZL}.

[3] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

[4] t_t is the same as t_{THL} and t_{TLH}.

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms

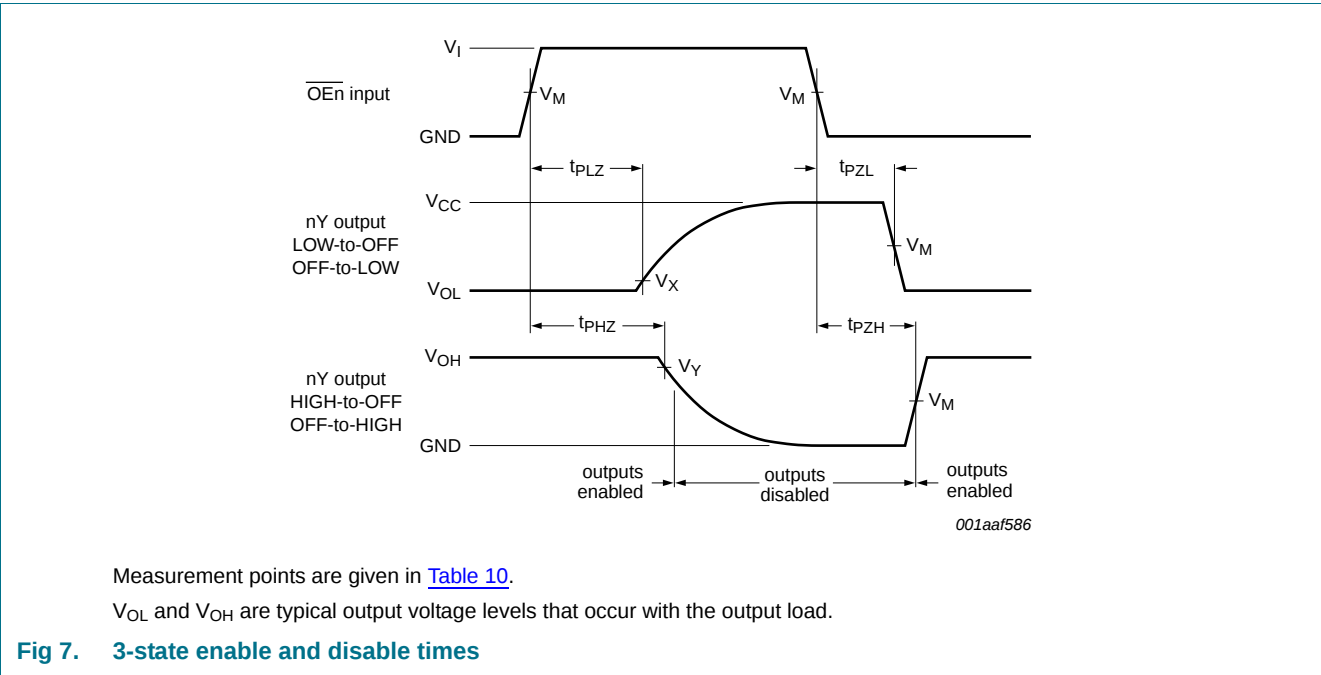
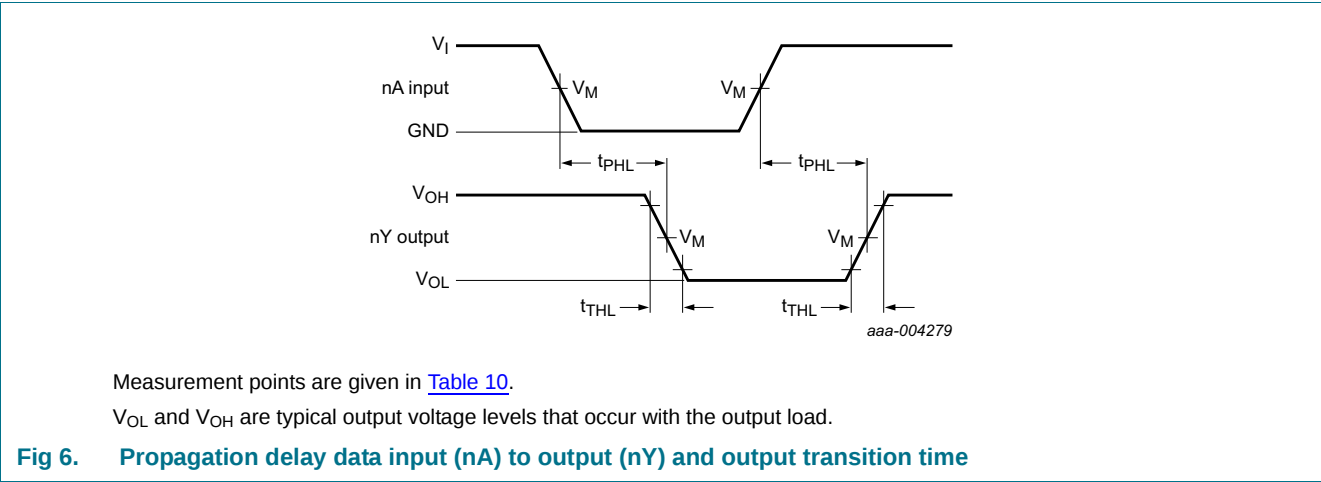
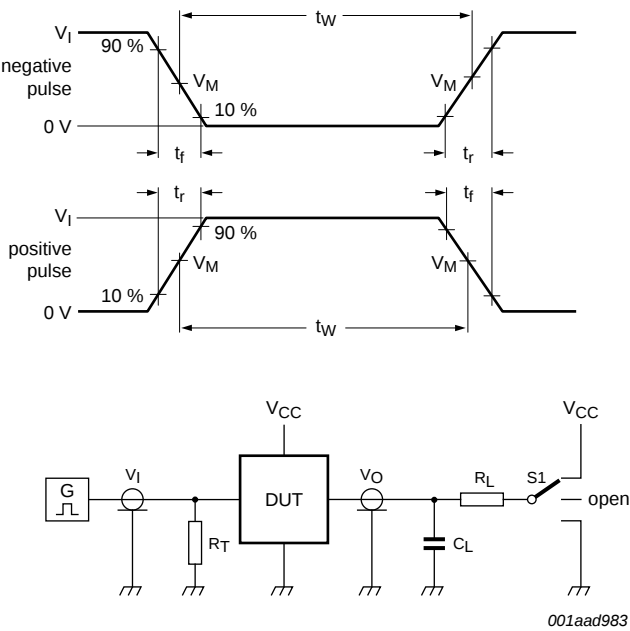


Table 10. Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC365-Q100	$0.5V_{CC}$	$0.5V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$
74HCT365-Q100	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$



Test data is given in [Table 11](#).
Definitions test circuit:
 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator
 C_L = Load capacitance including jig and probe capacitance
 R_L = Load resistor
 $S1$ = Test selection switch

Fig 8. Load circuitry for measuring switching times

Table 11. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC365-Q100	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT365-Q100	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

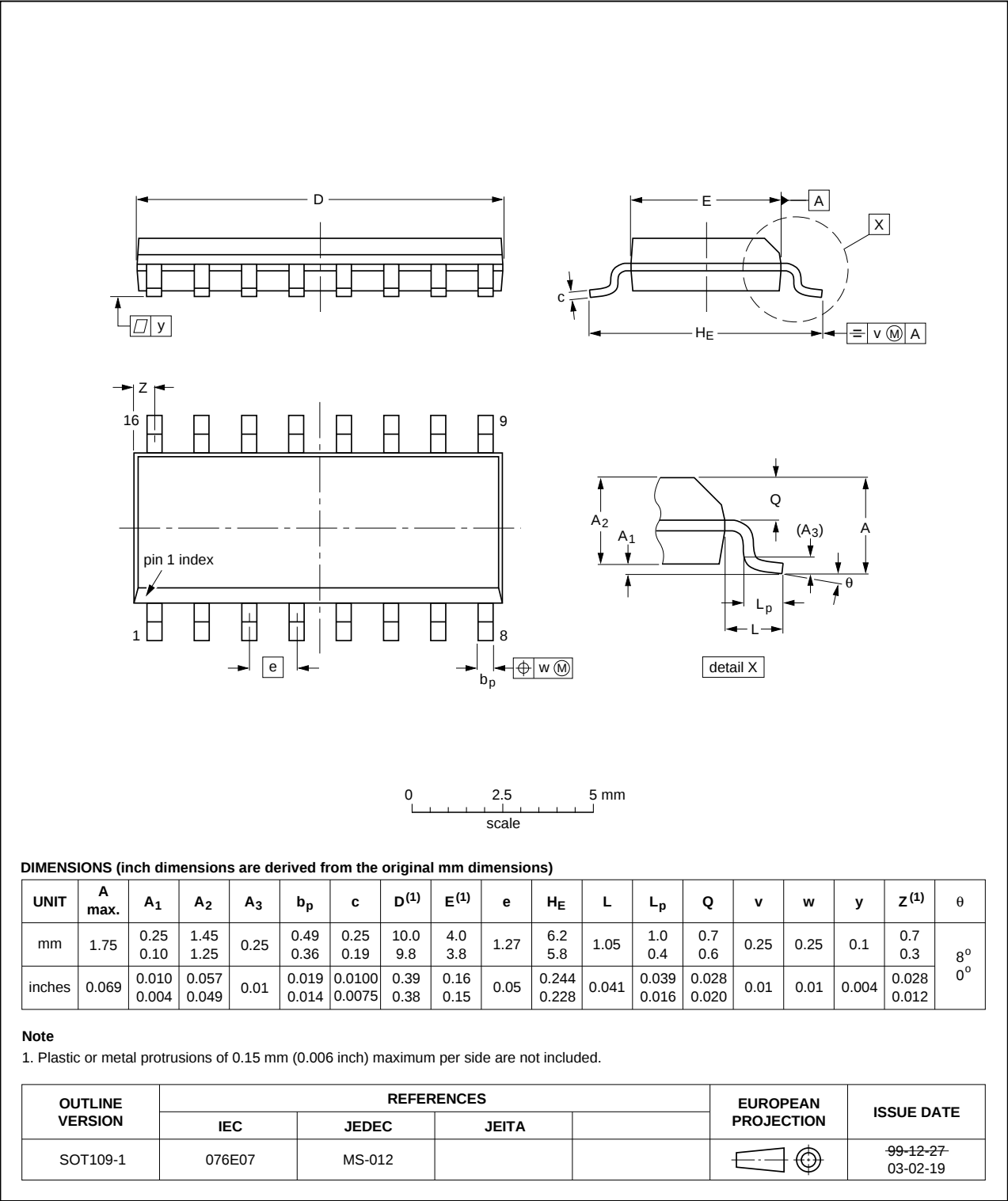


Fig 9. Package outline SOT109-1 (SO16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

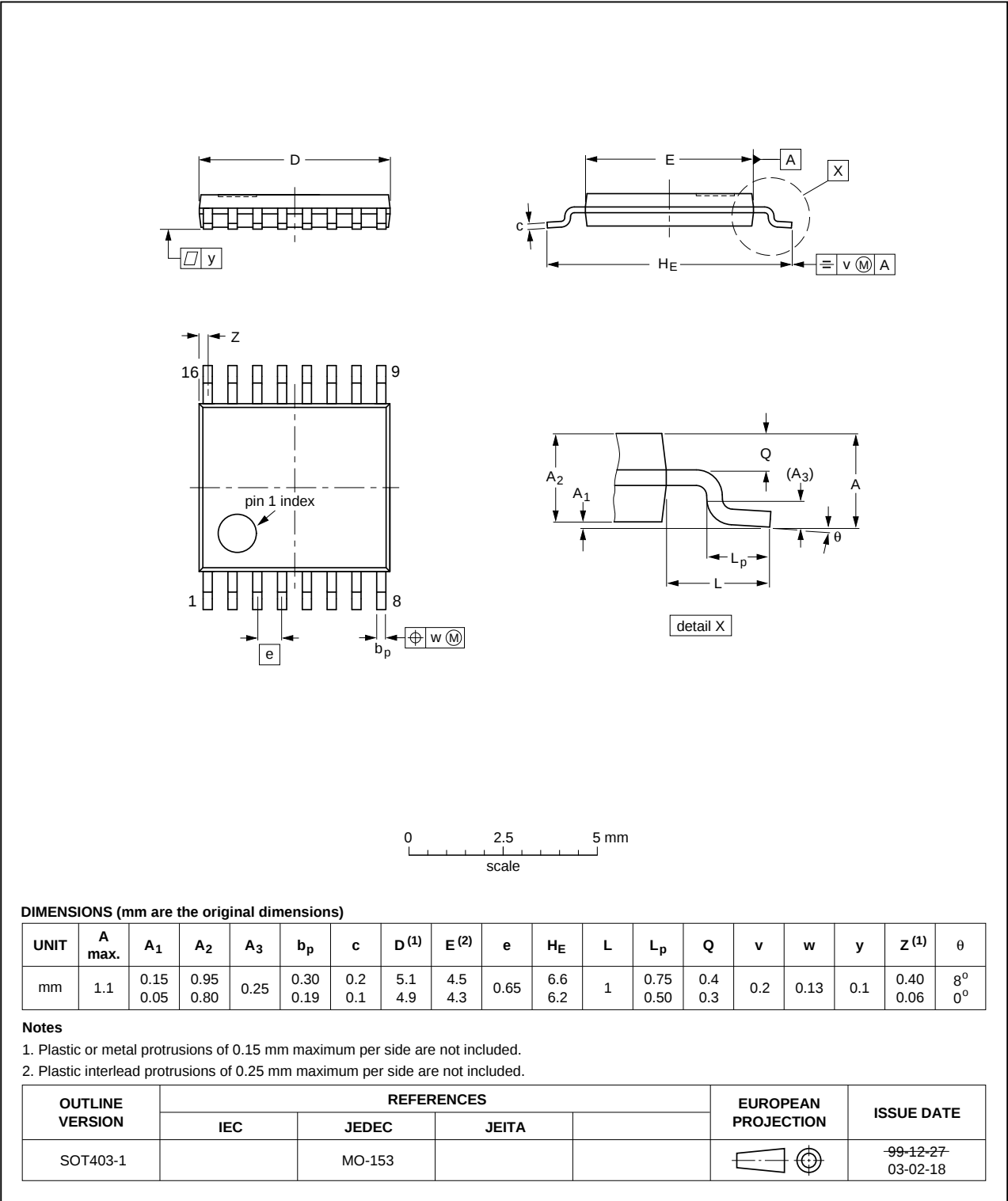


Fig 10. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
MIL	Military

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT365_Q100 v.1	20120802	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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